
HZS-L Series

Silicon Epitaxial Planar Zener Diode for Low Noise Application

HITACHI

ADE-208-121A(Z)

Rev 1

Dec. 1996

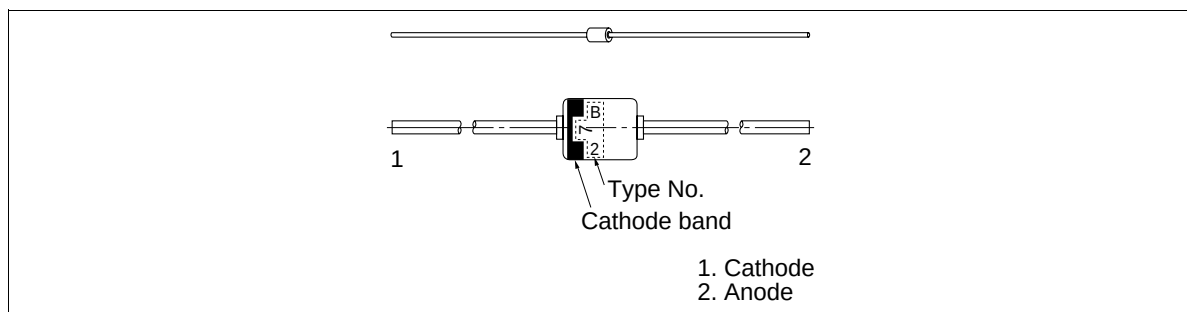
Features

- Diode noise level of this series is approximately 1/3-1/10 lower than the HZ series.
- Low leakage, low zener impedance and maximum power dissipation of 400 mW are ideally suited for stabilized power supply, etc.
- Wide spectrum from 5.2V through 38V of zener voltage provide flexible application.
- Suitable for 5mm-pitch high speed automatic insertion.

Ordering Information

Type No.	Mark	Package Code
HZS-L Series	Type No.	MHD

Outline



HZS-L Series

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Power dissipation	Pd	400	mW
Junction temperature	Tj	200	°C
Storage temperature	Tstg	-55 to +175	°C

Electrical Characteristics (Ta = 25°C)

		Zener Voltage		Reverse Current		Dynamic Resistance		
		VZ (V)*1		Test Condition	IR (μA)	Test Condition	rd (Ω)	Test Condition
Type	Grade	Min	Max	IZ (mA)	Max	VR (V)	Max	IZ (mA)
HZS6L	A1	5.2	5.5	0.5	1	2.0	150	0.5
	A2	5.3	5.6					
	A3	5.4	5.7					
	B1	5.5	5.8				80	0.5
	B2	5.6	5.9					
	B3	5.7	6.0					
	C1	5.8	6.1				60	0.5
	C2	6.0	6.3					
	C3	6.1	6.4					
HZS7L	A1	6.3	6.6	0.5	1	3.5	60	0.5
	A2	6.4	6.7					
	A3	6.6	6.9					
	B1	6.7	7.0					
	B2	6.9	7.2					
	B3	7.0	7.3					
	C1	7.2	7.6					
	C2	7.3	7.7					
	C3	7.5	7.9					
HZS9L	A1	7.7	8.1	0.5	1	6.0	60	0.5
	A2	7.9	8.3					
	A3	8.1	8.5					

Note: 1. Tested with DC.

HZS-L Series								
Type	Grade	Zener Voltage		Reverse Current		Dynamic Resistance		
		VZ (V)*1		Test Condition	IR (μA)	Test Condition	rd (Ω)	Test Condition
		Min	Max	IZ (mA)	Max	VR (V)	Max	IZ (mA)
HZS9L	B1	8.3	8.7	0.5	1	6.0	60	0.5
	B2	8.5	8.9					
	B3	8.7	9.1					
	C1	8.9	9.3					
	C2	9.1	9.5					
	C3	9.3	9.7					
HZS11L	A1	9.5	9.9	0.5	1	8.0	80	0.5
	A2	9.7	10.1					
	A3	9.9	10.3					
	B1	10.2	10.6					
	B2	10.4	10.8					
	B3	10.7	11.1					
	C1	10.9	11.3					
	C2	11.1	11.6					
	C3	11.4	11.9					
HZS12L	A1	11.6	12.1	0.5	1	10.5	80	0.5
	A2	11.9	12.4					
	A3	12.2	12.7					
	B1	12.4	12.9					
	B2	12.6	13.1					
	B3	12.9	13.4					
	C1	13.2	13.7					
	C2	13.5	14.0					
	C3	13.8	14.3					
HZS15L	1	14.1	14.7	0.5	1	13.0	80	0.5
	2	14.5	15.1					
	3	14.9	15.5					
HZS16L	1	15.3	15.9	0.5	1	14.0	80	0.5
	2	15.7	16.5					
	3	16.3	17.1					

Note: 1. Tested with DC.

HZS-L Series

		Zener Voltage		Reverse Current		Dynamic Resistance		
		VZ (V)*1		Test Condition	IR (μA)	Test Condition	rd (Ω)	Test Condition
Type	Grade	Min	Max	IZ (mA)	Max	VR (V)	Max	IZ (mA)
HZS18L	1	16.9	17.7	0.5	1	15.0	80	0.5
	2	17.5	18.3					
	3	18.1	19.0					
HZS20L	1	18.8	19.7	0.5	1	18.0	100	0.5
	2	19.5	20.4					
	3	20.2	21.1					
HZS22L	1	20.9	21.9	0.5	1	20.0	100	0.5
	2	21.6	22.6					
	3	22.3	23.3					
HZS24L	1	22.9	24.0	0.5	1	22.0	120	0.5
	2	23.6	24.7					
	3	24.3	25.5					
HZS27L	1	25.2	26.6	0.5	1	24.0	150	0.5
	2	26.2	27.6					
	3	27.2	28.6					
HZS30L	1	28.2	29.6	0.5	1	27.0	200	0.5
	2	29.2	30.6					
	3	30.2	31.6					
HZS33L	1	31.2	32.6	0.5	1	30.0	250	0.5
	2	32.2	33.6					
	3	33.2	34.6					
HZS36L	1	34.2	35.7	0.5	1	33.0	300	0.5
	2	35.3	36.8					
	3	36.4	38.0					

Note: 1. Tested with DC.

Note: 2. Type No. is as follows; HZS6A1L, HZS6A2L, HZS36-3L

Main Characteristic

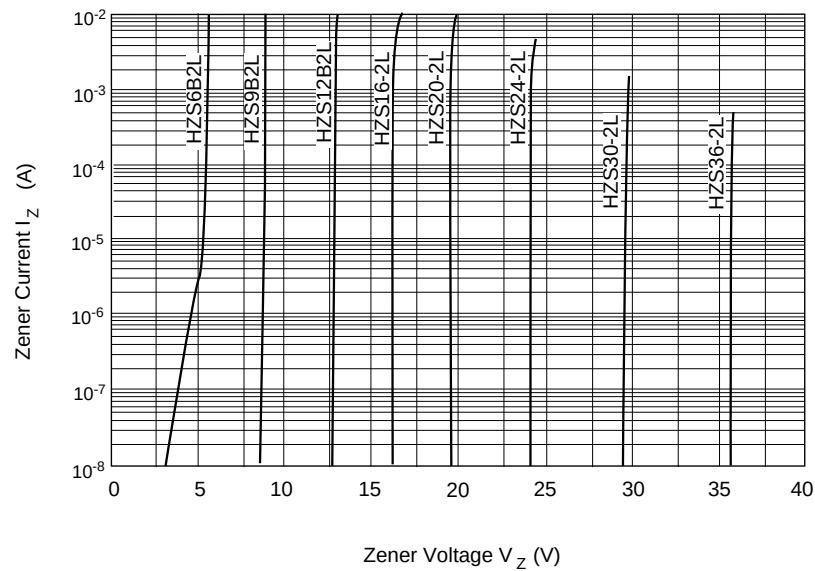


Fig.1 Zener current Vs. Zener voltage

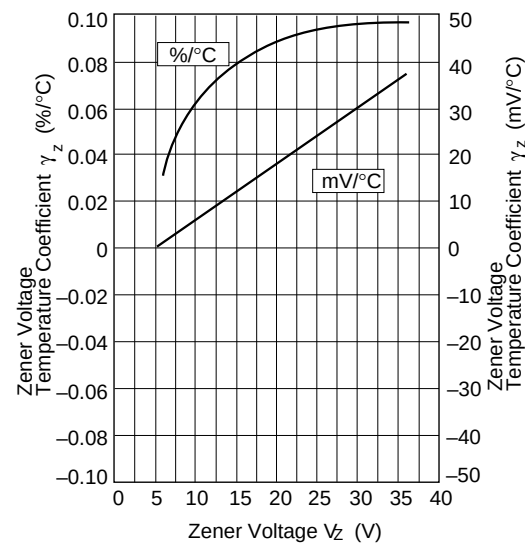


Fig.2 Temperature Coefficient Vs. Zener voltage

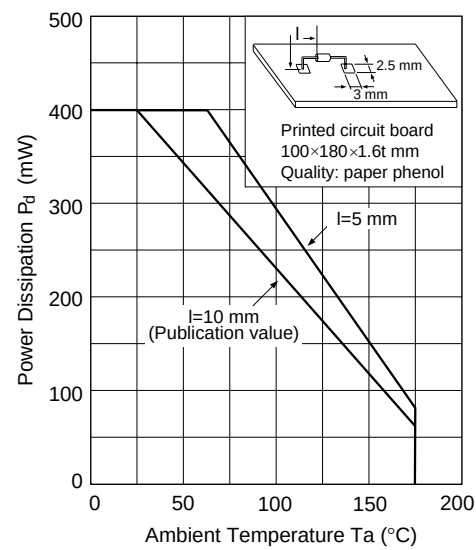


Fig.3 Power Dissipation Vs. Ambient Temperature

HZS-L Series

Package Dimensions

Unit : mm

